

## 7<sup>th</sup> International Workshop on Compact Modeling

Room 201B, Taipei International Convention Center (TICC), Taipei, Taiwan  
January 18, 2010

### Advance Program

On-site Registration: 8:00 – 9:00 am, Room 201B, TICC, registration fee: US\$30

Session 1 (9:00 – 11:40am), Chairs: Zhiping Yu (Tsinghua U, Beijing) & Young June Park (SNU)

(9:00 – 9:05) Opening Remark, M. Miura-Mattausch (Hiroshima U), Workshop Co-Chair

1. (9:05 – 9:35am) Goichi Yokomizo and Hiroo Masuda (STARC) (Invited), “STARC-QA on compact model and parameters”
2. (9:35 – 10:00am) Jian Zhang, Jin He (Peking U), “A charge-based non-quasi-static transient model for SOI MOSFETs”

(10:00 – 10:20am) Coffee Break

3. (10:20 – 10:50am) James B. Kuo, J. S. Su, D. Chen, and C. S. Yeh (Nat'l Taiwan U & UMC) (Invited), “Compact Modeling of the 40nm PD SOI NMOS Device Via SPICE BJT/MOS Model Approach Considering the Floating-Body Effect”
4. (10:50 – 11:15am) Ze Yuan and Zhiping Yu, (Tsinghua U, Beijing) “Comprehensive modeling of subthreshold swing and threshold voltage roll-off for short-channel double-gate MOSFETs”
5. (11:15 – 11:40am) K. Ishimura, S. Kusu, and M. Miura-Mattausch (Hiroshima U), “Compact model HiSIM-DG valid for independent DG-MOSFETs structures”

(11:40am – 1:00pm) Lunch Break

Session 2 (1:00pm – 4:45pm), Chairs: M. Miura-Mattausch (Hiroshima U) & Jin He (Peking U)

1. (1:00 – 1:30pm) Darsen Lu, Chung-Hsun Lin, Ali Niknejad, Chenming Hu (UC Berkeley) (Invited), “A Multi-Gate CMOS Compact Model – BSIMMG”
2. (1:30 – 1:55pm) Bastien Cousin, Marina Reyboz<sup>1</sup>, Olivier Rozeau<sup>1</sup>, Marie-Anne Jaud, and Jalal Jomaah, (LETI, Minatec, France), “A compact model of short channel effects for undoped cylindrical gate-all-around MOSFETs”
3. (1:55 – 2:20pm) Sooyoung Park, and Young June Park (SNU), “A new strategy for modeling of mobility limited by discrete charge effects in scaled MOSFETs”
4. (2:20 – 2:45pm) Chi Liu, et al., Jin He (Peking U), “Signal transient response compact modeling of the dispersionless interconnect with capacitive and inductive load terminals”

(2:45 – 3:00pm) Coffee Break

5. (3:00 – 3:30pm) Weidong Liu (Synopsys) (Invited) Topic to be announced
6. (3:30 – 3:55pm) Reiji Takashina and Zhong Wang (NEC/Synopsys), “TCAD-based compact model parameter extraction for VBIC”
7. (3:55 – 4:20pm) Y. Shintaku, S. Kusu, G. Suzuki, K. Konno, and M. Miura-Mattausch (Hiroshima U), “Modeling of photocurrent for high performance optoelectric circuit simulation”
8. (4:20 – 4:45pm) Huang Wang, Lingling Sun, Jun Liu, Huanhuan Zou, Zhiping Yu, and Jianjun Gao (Hangzhou Dianzi University, China) “Comparisons of modeling approaches for RF CMOS spiral inductors”

4:45pm: Closing Remark, Zhiping Yu (Tsinghua U, Beijing) Co-Chair